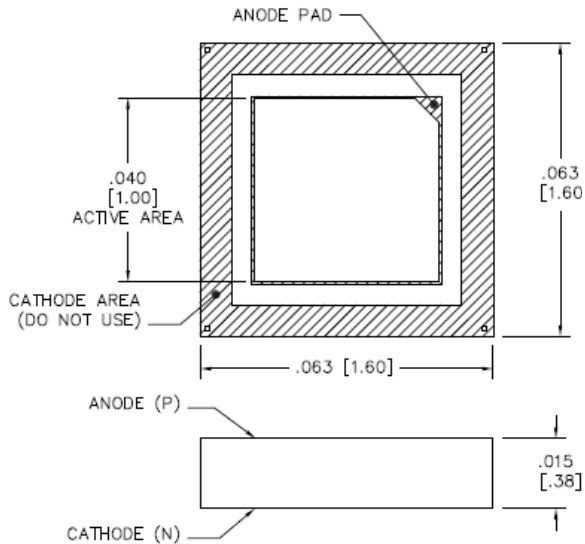


FEATURES



- Red to Near Infrared Enhanced Photodiode
- Photosensitive active area: 1mm x 1mm
- High Sensitivity:
0.62A/W ($\lambda=850\text{nm}$), 0.35A/W ($\lambda=1064\text{nm}$)
- Wide Operating Temperature: -40°C TO +125°C
- Ideal for Laser Monitoring Applications
- RoHS and REACH Compliant

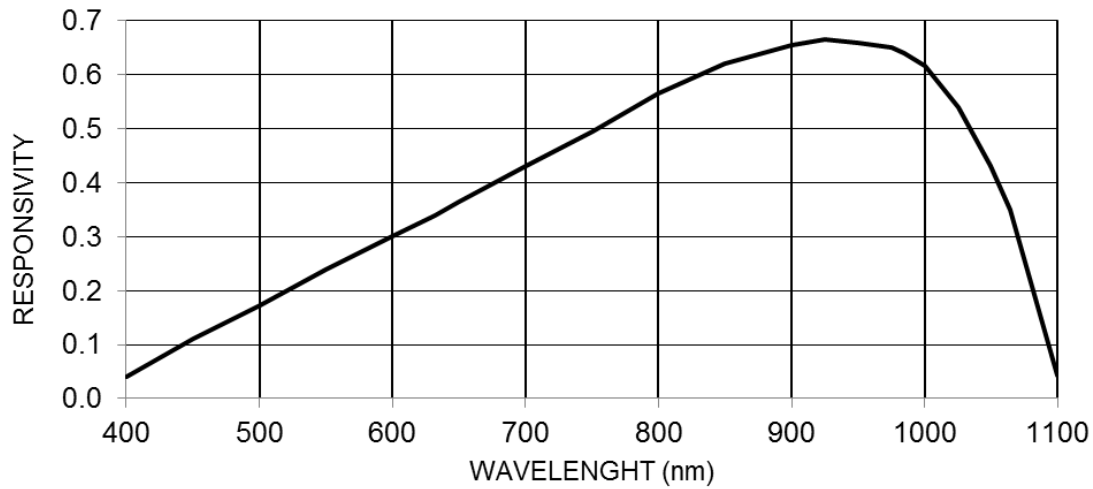
ELECTRO-OPTICAL CHARACTERISTICS AT 25°C

PARAMETERS	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Active Area			1		mm ²
Spectral Response Range λ		320		1100	nm
Responsivity, \mathcal{R}	@ 850nm		.62		A/W
Responsivity, \mathcal{R}	@ 1064nm		.35		A/W
Dark Current, I_{dr}	$V_r = 3V$		0.1	0.75	nA
Shunt Resistance	$V_R = 10mV$	200	500		M Ω
Reverse Breakdown Voltage, V_R	$I_R = 1\mu A$	50			Volts
Capacitance, C	$V_R = 0V$		3		pF
Rise Time	$V_R = 5V$		50		nsec

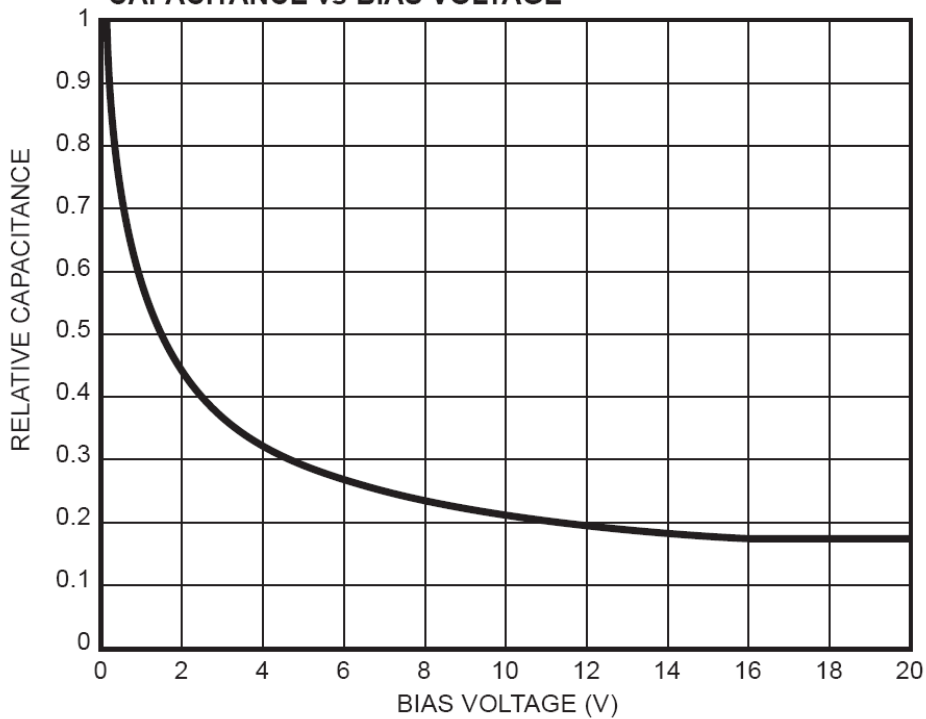
THERMAL PARAMETERS

Storage and Operating Temperature Range	-40°C TO 125°C
Maximum Junction Temperature	125°C

TYPICAL SPECTRAL RESPONSE



CAPACITANCE vs BIAS VOLTAGE



ORDERING INFORMATION

ODD-1064-004-1 Waffle Pack
ODD-1064-004-2 Grip Ring